

FEATURES

- Complete monolithic resolver-to-digital converter
- 3125 rps maximum tracking rate (10-bit resolution)
- ±2.5 arc minutes of accuracy
- 10-/12-/14-/16-bit resolution, set by user
- Parallel and serial 10-bit to 16-bit data ports
- Absolute position and velocity outputs
- System fault detection
- Programmable fault detection thresholds
- Differential inputs
- Incremental encoder emulation
- Programmable sinusoidal oscillator on-board
- Compatible with DSP and SPI interface standards
- 5.0 V supply with 2.3 V to 5 V logic interface
- 55°C to +125°C temperature rating

APPLICATIONS

- DC and ac servo motor controls
- Encoder emulation
- Electric power steering
- Electric vehicles
- Integrated starter generators/alternators
- Automotive motion sensing and controls

GENERAL DESCRIPTION

The [AD2S1210-KGD-CHIPS](#) is a complete 10-bit to 16-bit resolution tracking resolver-to-digital (R/D) converter, integrating an on-board programmable sinusoidal oscillator that provides sine wave excitation for resolvers.

The converter accepts 3.15 V p-p ± 27% input signals, in the range of 2 kHz to 20 kHz on the sine and cosine inputs. A Type II servo loop is employed to track the inputs and convert the input sine and cosine information into a digital representation of the input angle and velocity. The maximum tracking rate is 3125 rps.

Additional application and technical information can be found in the [AD2S1210](#) data sheet.

Known Good Die (KGD): these die are fully guaranteed to data sheet specifications.

Rev. 0

[Document Feedback](#)

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FUNCTIONAL BLOCK DIAGRAM

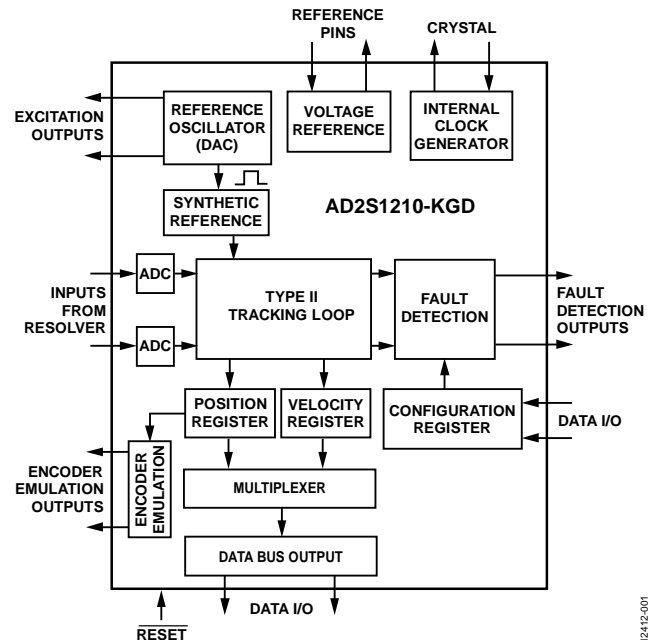


Figure 1.

PRODUCT HIGHLIGHTS

1. Ratiometric tracking conversion. The Type II tracking loop provides continuous output position data without conversion delay. It also provides noise immunity and tolerance of harmonic distortion on the reference and input signals.
2. System fault detection. A fault detection circuit can sense loss of resolver signals, out-of-range input signals, input signal mismatch, or loss of position tracking. The fault detection threshold levels can be individually programmed by the user for optimization within a particular application.
3. Input signal range. The sine and cosine inputs can accept differential input voltages of 3.15 V p-p ± 27%.
4. Programmable excitation frequency. Excitation frequency is easily programmable to a number of standard frequencies between 2 kHz and 20 kHz.
5. Triple format position data. Absolute 10-bit to 16-bit angular position data is accessed via either a 16-bit parallel port or a 4-wire serial interface. Incremental encoder emulation is in standard A-quadrant-B format with direction output available.
6. Digital velocity output. 10-bit to 16-bit signed digital velocity accessed via either a 16-bit parallel port or a 4-wire serial interface.

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REVISION HISTORY

6/14—Revision 0: Initial Version

SPECIFICATIONS

$AV_{DD} = DV_{DD} = 5.0 \text{ V} \pm 5\%$ and $CLKIN = 8.192 \text{ MHz} \pm 25\%$. \overline{EXC} , \overline{EXC} frequency = 10 kHz to 20 kHz (10-bit), 6 kHz to 20 kHz (12-bit), 3 kHz to 12 kHz (14-bit), and 2 kHz to 10 kHz (16-bit). $T_A = T_{MIN}$ to T_{MAX} , unless otherwise noted. Devices are guaranteed to the data sheet by wafer probing at 25°C. Characterization at temperature performed in released package formats. Temperature range is as follows: -55°C to +125°C.

Table 1.

Parameter	Min	Typ	Max	Unit	Test Conditions/Comments
SINE, COSINE INPUTS¹					
Voltage Amplitude	2.3	3.15	4.0	V p-p	Sinusoidal waveforms, differential SIN to SINLO, COS to COSLO
Input Bias Current			8.25	μA	$V_{IN} = 4.0 \text{ V p-p}$, $CLKIN = 8.192 \text{ MHz}$
Input Impedance	485			kΩ	$V_{IN} = 4.0 \text{ V p-p}$, $CLKIN = 8.192 \text{ MHz}$
Phase Lock Range	-44		+44	Degrees	Sine/cosine vs. EXC output, Control Register D3 = 0
Common-Mode Rejection		±20		arc sec/V	10 Hz to 1 MHz, Control Register D4 = 0
ANGULAR ACCURACY²					
Angular Accuracy		±2.5 + 1 LSB	±7 + 1 LSB	arc min	No missing codes
Resolution		10, 12, 14, 16		Bits	
Integral Nonlinearity (INL)					
10-Bit			±1	LSB	
12-Bit			±2	LSB	
14-Bit			±4	LSB	
16-Bit			±16	LSB	
Differential Nonlinearity (DNL)			±0.9	LSB	
Repeatability		±1		LSB	
VELOCITY OUTPUT					
Velocity Accuracy ³					
10-Bit			±2	LSB	Zero acceleration
12-Bit			±2	LSB	
14-Bit			±4	LSB	
16-Bit			±16	LSB	
Resolution ⁴		9, 11, 13, 15		Bits	
DYNAMNIC PERFORMANCE					
Bandwidth					
10-Bit	2000		6600	Hz	CLKIN = 8.192 MHz
	2900		5400	Hz	
12-Bit	900		2800	Hz	CLKIN = 8.192 MHz
	1200		2200	Hz	
14-Bit	400		1500	Hz	CLKIN = 8.192 MHz
	600		1200	Hz	
16-Bit	100		350	Hz	CLKIN = 8.192 MHz
	125		275	Hz	
Tracking Rate					
10-Bit			3125	rps	CLKIN = 10.24 MHz
			2500		CLKIN = 8.192 MHz
12-Bit			1250	rps	CLKIN = 10.24 MHz
			1000		CLKIN = 8.192 MHz
14-Bit			625	rps	CLKIN = 10.24 MHz
			500		CLKIN = 8.192 MHz
16-Bit			156.25	rps	CLKIN = 10.24 MHz
			125		CLKIN = 8.192 MHz

Parameter	Min	Typ	Max	Unit	Test Conditions/Comments
Acceleration Error					
10-Bit		30		arc min	At 50,000 rps ² , CLKIN = 8.192 MHz
12-Bit		30		arc min	At 10,000 rps ² , CLKIN = 8.192 MHz
14-Bit		30		arc min	At 2500 rps ² , CLKIN = 8.192 MHz
16-Bit		30		arc min	At 125 rps ² , CLKIN = 8.192 MHz
Settling Time 10° Step Input					
10-Bit		0.6	0.9	ms	To settle to within ±2 LSB, CLKIN = 8.192 MHz
12-Bit		2.2	3.3	ms	To settle to within ±2 LSB, CLKIN = 8.192 MHz
14-Bit		6.5	9.8	ms	To settle to within ±2 LSB, CLKIN = 8.192 MHz
16-Bit		27.5	48	ms	To settle to within ±2 LSB, CLKIN = 8.192 MHz
Settling Time 179° Step Input					
10-Bit		1.5	2.4	ms	To settle to within ±2 LSB, CLKIN = 8.192 MHz
12-Bit		4.75	6.1	ms	To settle to within ±2 LSB, CLKIN = 8.192 MHz
14-Bit		10.5	15.2	ms	To settle to within ±2 LSB, CLKIN = 8.192 MHz
16-Bit		45	68	ms	To settle to within ±2 LSB, CLKIN = 8.192 MHz
EXC, EXC [¯] OUTPUTS					
Voltage	3.2	3.6	4.0	V p-p	Load ±100 μA, typical differential output (EXC to EXC [¯]) = 7.2 V p-p
Center Voltage	2.40	2.47	2.53	V	
Frequency	2		20	kHz	
EXC/EXC [¯] DC Mismatch			30	mV	
EXC/EXC [¯] AC Mismatch			132	mV	
Total Harmonic Distortion (THD)		-58		dB	First five harmonics
VOLTAGE REFERENCE					
REFOUT	2.40	2.47	2.53	V	±I _{OUT} = 100 μA
Drift		100		ppm/°C	
Power Supply Rejection Ratio (PSRR)		-60		dB	
CLKIN, XTALOUT ⁵					
V _{IL} Voltage Input Low			0.8	V	
V _{IH} Voltage Input High	2.0			V	
LOGIC INPUTS					
V _{IL} Voltage Input Low			0.8	V	V _{DRIVE} = 2.7 V to 5.25 V
V _{IH} Voltage Input High	2.0		0.7	V	V _{DRIVE} = 2.3 V to 2.7 V
I _{IL} Low Level Input Current (Nonpull-Up)			10	μA	V _{DRIVE} = 2.7 V to 5.25 V
I _{IL} Low Level Input Current (Pull-Up)			80	μA	V _{DRIVE} = 2.3 V to 2.7 V
I _{IH} High Level Input Current	-10			μA	RES0, RES1, [¯] RD, [¯] WR/ [¯] FSYNC, A0, A1, and RESET pins
LOGIC OUTPUTS					
V _{OL} Voltage Output Low			0.4	V	V _{DRIVE} = 2.3 V to 5.25 V
V _{OH} Voltage Output High	2.4			V	V _{DRIVE} = 2.7 V to 5.25 V
I _{OZH} High Level Three-State Leakage	2.0			V	V _{DRIVE} = 2.3 V to 2.7 V
I _{OZL} Low Level Three-State Leakage	-10		10	μA	
POWER REQUIREMENTS					
AV _{DD}	4.75		5.25	V	
DV _{DD}	4.75		5.25	V	
V _{DRIVE}	2.3		5.25	V	

Parameter	Min	Typ	Max	Unit	Test Conditions/Comments
POWER SUPPLY					
I _{AVDD}			12	mA	
I _{DVDD}			35	mA	
I _{OVDD}			2	mA	

¹ The voltages, SIN, SINLO, COS, and COSLO, relative to AGND, must always be between 0.15 V and AV_{DD} – 0.2 V.

² All specifications within the angular accuracy parameter are tested at constant velocity, that is, zero acceleration.

³ The velocity accuracy specification includes velocity offset and dynamic ripple.

⁴ For example, when RES0 = 0 and RES1 = 1, the position output has a resolution of 12 bits. The velocity output has a resolution of 11 bits with the MSB indicating the direction of rotation. In this example, with a CLKIN frequency of 8.192 MHz, the velocity LSB is 0.488 rps, that is, 1000 rps/(2¹¹).

⁵ The clock frequency of the AD2S1210-KGD-CHIPS can be supplied with a crystal, an oscillator, or directly from a DSP/microprocessor digital output. When using a single-ended clock signal directly from the DSP/microprocessor, the XTALOUT pin must remain open circuit, and the logic levels outlined under the logic inputs parameter in Table 1 apply.

TIMING SPECIFICATIONS

AV_{DD} = DV_{DD} = 5.0 V ± 5%, T_A = T_{MIN} to T_{MAX}, unless otherwise noted.

Table 2.

Parameter	Description	Limit at T _{MIN} , T _{MAX}	Unit
f _{CLKIN}	Frequency of clock input	6.144 10.24	MHz min MHz max
t _{CK}	Clock period (= 1/f _{CLKIN})	98 163	ns min ns max
t ₁	A0 and A1 setup time before $\overline{RD}/\overline{CS}$ low	2	ns min
t ₂	Delay \overline{CS} falling edge to $\overline{WR}/\overline{FSYNC}$ rising edge	22	ns min
t ₃	Address/data setup time during a write cycle	3	ns min
t ₄	Address/data hold time during a write cycle	2	ns min
t ₅	Delay $\overline{WR}/\overline{FSYNC}$ rising edge to \overline{CS} rising edge	2	ns min
t ₆	Delay \overline{CS} rising edge to \overline{CS} falling edge	10	ns min
t ₇	Delay between writing address and writing data	2 × t _{CK} + 20	ns min
t ₈	A0 and A1 hold time after $\overline{WR}/\overline{FSYNC}$ rising edge	2	ns min
t ₉	Delay between successive write cycles	6 × t _{CK} + 20	ns min
t ₁₀	Delay between rising edge of $\overline{WR}/\overline{FSYNC}$ and falling edge of \overline{RD}	2	ns min
t ₁₁	Delay \overline{CS} falling edge to \overline{RD} falling edge	2	ns min
t ₁₂	Enable delay \overline{RD} low to data valid in configuration mode V _{DRIVE} = 4.5 V to 5.25 V V _{DRIVE} = 2.7 V to 3.6 V V _{DRIVE} = 2.3 V to 2.7 V	37 25 30	ns min ns min ns min
t ₁₃	\overline{RD} rising edge to \overline{CS} rising edge	2	ns min
t _{14A}	Disable delay \overline{RD} high to data high-Z	16	ns min
t _{14B}	Disable delay \overline{CS} high to data high-Z	16	ns min
t ₁₅	Delay between rising edge of \overline{RD} and falling edge of $\overline{WR}/\overline{FSYNC}$	2	ns min
t ₁₆	\overline{SAMPLE} pulse width	2 × t _{CK} + 20	ns min
t ₁₇	Delay from \overline{SAMPLE} before $\overline{RD}/\overline{CS}$ low	6 × t _{CK} + 20	ns min
t ₁₈	Hold time \overline{RD} before \overline{RD} low	2	ns min
t ₁₉	Enable delay $\overline{RD}/\overline{CS}$ low to data valid V _{DRIVE} = 4.5 V to 5.25 V V _{DRIVE} = 2.7 V to 3.6 V V _{DRIVE} = 2.3 V to 2.7 V	17 21 33	ns min ns min ns min
t ₂₀	\overline{RD} pulse width	6	ns min
t ₂₁	A0 and A1 set time to data valid when $\overline{RD}/\overline{CS}$ low V _{DRIVE} = 4.5 V to 5.25 V V _{DRIVE} = 2.7 V to 3.6 V V _{DRIVE} = 2.3 V to 2.7 V	36 37 29	ns min ns min ns min

Parameter	Description	Limit at T _{MIN} , T _{MAX}	Unit
t ₂₂	Delay $\overline{WR}/\overline{FSYNC}$ falling edge to SCLK rising edge	3	ns min
t ₂₃	Delay $\overline{WR}/\overline{FSYNC}$ falling edge to SDO release from high-Z		
	V _{DRIVE} = 4.5 V to 5.25 V	16	ns min
	V _{DRIVE} = 2.7 V to 3.6 V	26	ns min
	V _{DRIVE} = 2.3 V to 2.7 V	29	ns min
t ₂₄	Delay SCLK rising edge to DBx valid		
	V _{DRIVE} = 4.5 V to 5.25 V	24	ns min
	V _{DRIVE} = 2.7 V to 3.6 V	18	ns min
	V _{DRIVE} = 2.3 V to 2.7 V	32	ns min
t ₂₅	SCLK high time	0.4 × t _{SCLK}	ns min
t ₂₆	SCLK low time	0.4 × t _{SCLK}	ns min
t ₂₇	SDI setup time prior to SCLK falling edge	3	ns min
t ₂₈	SDI hold time after SCLK falling edge	2	ns min
t ₂₉	Delay $\overline{WR}/\overline{FSYNC}$ rising edge to SDO high-Z	15	ns min
t ₃₀	Delay from \overline{SAMPLE} before $\overline{WR}/\overline{FSYNC}$ falling edge	6 × t _{CK} + 20 ns	ns min
t ₃₁	Delay \overline{CS} falling edge to $\overline{WR}/\overline{FSYNC}$ falling edge in normal mode	2	ns min
t ₃₂	A0 and A1 setup time before $\overline{WR}/\overline{FSYNC}$ falling edge	2	ns min
t ₃₃	A0 and A1 hold time after $\overline{WR}/\overline{FSYNC}$ falling edge ¹		
	In normal mode, A0 = 0, A1 = 0/1	24 × t _{SCLK} + 5 ns	ns min
	In configuration mode, A0 = 1, A1 = 1	8 × t _{SCLK} + 5 ns	ns min
t ₃₄	Delay $\overline{WR}/\overline{FSYNC}$ rising edge to $\overline{WR}/\overline{FSYNC}$ falling edge	10	ns min
f _{SCLK}	Frequency of SCLK input		
	V _{DRIVE} = 4.5 V to 5.25 V	20	MHz
	V _{DRIVE} = 2.7 V to 3.6 V	25	MHz
	V _{DRIVE} = 2.3 V to 2.7 V	15	MHz

¹ A0 and A1 must remain constant for the duration of the serial readback. This may require 24 clock periods to read back the 8-bit fault information in addition to the 16 bits of position/velocity data. If the fault information is not required, A0/A1 may be released following 16 clock cycles.

ABSOLUTE MAXIMUM RATINGS

Table 3.

Parameter	Rating
AV_{DD} to AGND, DGND	-0.3 V to +7.0 V
DV_{DD} to AGND, DGND	-0.3 V to +7.0 V
V_{DRIVE} to AGND, DGND	-0.3 V to AV_{DD}
AV_{DD} to DV_{DD}	-0.3 V to +0.3 V
AGND to DGND	-0.3 V to +0.3 V
Analog Input Voltage to AGND	-0.3 V to $AV_{DD} + 0.3$ V
Digital Input Voltage to DGND	-0.3 V to $V_{DRIVE} + 0.3$ V
Digital Output Voltage to DGND	-0.3 V to $V_{DRIVE} + 0.3$ V
Analog Output Voltage Swing	-0.3 V to $AV_{DD} + 0.3$ V
Input Current to Any Pin Except Supplies ¹	±10 mA
Operating Temperature Range (Ambient)	-55°C to +125°C
Storage Temperature Range	-65°C to +150°C
ESD	2 kV HBM

¹ Transient currents of up to 100 mA do not cause latch-up.

Stresses at or above those listed under Absolute Maximum Ratings may cause permanent damage to the product. This is a stress rating only; functional operation of the product at these or any other conditions above those indicated in the operational section of this specification is not implied. Operation beyond the maximum operating conditions for extended periods may affect product reliability.

ESD CAUTION



ESD (electrostatic discharge) sensitive device. Charged devices and circuit boards can discharge without detection. Although this product features patented or proprietary protection circuitry, damage may occur on devices subjected to high energy ESD. Therefore, proper ESD precautions should be taken to avoid performance degradation or loss of functionality.

PIN CONFIGURATION AND FUNCTION DESCRIPTIONS

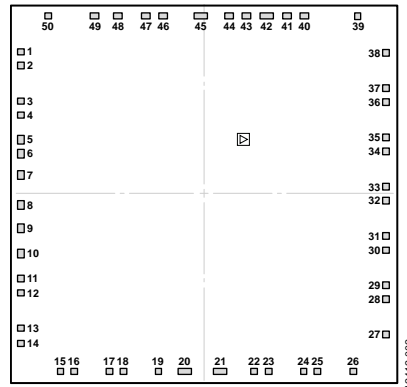


Figure 2. Pad Configuration

Table 4. Pad Function Descriptions

Pad No.	X-Axis (μm)	Y-Axis (μm)	Mnemonic	Pad Type	Description
1	-1870	+1453	RES1	Single	Resolution Select 1. Logic input. RES1 in conjunction with RES0 allows the programming of the resolution of the AD2S1210-KGD-CHIPS .
2	-1870	+1309	\overline{CS}	Single	Chip Select. Active low logic input. When \overline{CS} is held low, the device is enabled.
3	-1870	+948	\overline{RD}	Single	Edge-Triggered Logic Input. When the \overline{SOE} pin is high, \overline{RD} acts as a frame synchronization signal and output enable for the parallel data outputs, DB15 to DB0. The output buffer is enabled when \overline{CS} and \overline{RD} are held low. When the \overline{SOE} pin is low, hold the \overline{RD} pin high.
4	-1870	+805	$\overline{WR}/\overline{FSYNC}$	Single	Edge-Triggered Logic Input. When the \overline{SOE} pin is high, \overline{WR} acts as an input enable for the parallel data inputs, DB7 to DB0. When the \overline{SOE} pin is low, the \overline{FSYNC} pin acts as a frame synchronization signal and enable for the serial data bus.
5	-1870	+550	DGND	Single	Digital Ground. This pin is a ground reference point for the digital circuitry on the AD2S1210-KGD-CHIPS . Refer all digital input signals to the DGND voltage. Both DGND pins can be connected to the AGND plane of a system. Ideally, the DGND and AGND voltages are at the same potential, and they must not be more than 0.3 V apart, even on a transient basis.
6	-1870	+410	DGND	Single	Digital Ground. This pin is a ground reference point for the digital circuitry on the AD2S1210-KGD-CHIPS . Refer all digital input signals to the DGND voltage. Both DGND pins can be connected to the AGND plane of a system. Ideally, the DGND and AGND voltages are at the same potential, and they must not be more than 0.3 V apart, even on a transient basis.
7	-1870	+191	DV _{DD}	Single	Digital Supply Voltage, 4.75 V to 5.25 V. This is the supply voltage for all digital circuitry on the AD2S1210-KGD-CHIPS . Ideally, the AV _{DD} and DV _{DD} voltages are at the same potential, and they must not be more than 0.3 V apart, even on a transient basis.
8	-1870	-117	DV _{DD}	Single	Digital Supply Voltage, 4.75 V to 5.25 V. This is the supply voltage for all digital circuitry on the AD2S1210-KGD-CHIPS . Ideally, the AV _{DD} and DV _{DD} voltages are at the same potential, and they must not be more than 0.3 V apart, even on a transient basis.
9	-1870	-351	CLKIN	Single	Clock Input. A crystal or oscillator can be used at the CLKIN and XTALOUT pins to supply the required clock frequency of the AD2S1210-KGD . Alternatively, a single-ended clock can be applied to the CLKIN pin. The input frequency of the AD2S1210-KGD-CHIPS is specified from 6.144 MHz to 10.24 MHz.

Pad No.	X-Axis (μm)	Y-Axis (μm)	Mnemonic	Pad Type	Description
10	-1870	-611	XTALOUT	Single	Crystal Output. When using a crystal or oscillator to supply the clock frequency to the AD2S1210-KGD-CHIPS , apply the crystal across the CLKIN and XTALOUT pins. When using a single-ended clock source, consider the XTALOUT pin a no connect pin.
11	-1870	-872	$\overline{\text{SOE}}$	Single	Serial Output Enable. Logic input. This pin enables either the parallel or serial interface. The serial interface is selected by holding the $\overline{\text{SOE}}$ pin low, and the parallel interface is selected by holding the $\overline{\text{SOE}}$ pin high.
12	-1870	-1016	$\overline{\text{SAMPLE}}$	Single	Sample Result. Logic input. Data is transferred from the position and velocity integrators to the position and velocity registers, after a high to low transition on the $\overline{\text{SAMPLE}}$ signal. The fault register is also updated after a high to low transition on the $\overline{\text{SAMPLE}}$ signal.
13	-1870	-1376	DB15/SDO	Single	Data Bit 15/Serial Data Output Bus. When the $\overline{\text{SOE}}$ pin is high, this pin acts as DB15, a three-state data output pin controlled by $\overline{\text{CS}}$ and $\overline{\text{RD}}$. When the $\overline{\text{SOE}}$ pin is low, this pin acts as SDO, the serial data output bus controlled by $\overline{\text{CS}}$ and $\overline{\text{WR/FSYNC}}$. Data is clocked out on the rising edge of SCLK.
14	-1870	-1535	DB14/SDI	Single	Data Bit 14/Serial Data Input Bus. When the $\overline{\text{SOE}}$ pin is high, this pin acts as DB14, a three-state data output pin controlled by $\overline{\text{CS}}$ and $\overline{\text{RD}}$. When the $\overline{\text{SOE}}$ pin is low, this pin acts as SDI, the serial data input bus controlled by $\overline{\text{CS}}$ and $\overline{\text{WR/FSYNC}}$. Data is clocked in on the falling edge of SCLK.
15	-1466	-1820	DB13/SCLK	Single	Data Bit 13/Serial Clock. In parallel mode, this pin acts as DB13, a three-state data output pin controlled by $\overline{\text{CS}}$ and $\overline{\text{RD}}$. In serial mode, this pin acts as the serial clock input.
16	-1323	-1820	DB12	Single	Data Bit 12. Three-state data output pin controlled by $\overline{\text{CS}}$ and $\overline{\text{RD}}$.
17	-962	-1820	DB11	Single	Data Bit 11. Three-state data output pin controlled by $\overline{\text{CS}}$ and $\overline{\text{RD}}$.
18	-819	-1820	DB10	Single	Data Bit 10. Three-state data output pin controlled by $\overline{\text{CS}}$ and $\overline{\text{RD}}$.
19	-458	-1820	DB9	Single	Data Bit 9. Three-state data output pin controlled by $\overline{\text{CS}}$ and $\overline{\text{RD}}$.
20A	-230	-1820	V _{DRIVE}	Double	Logic Power Supply Input. The voltage supplied at this pin determines at what voltage the interface operates. Decouple this pin to DGND. The voltage range on this pin is 2.3 V to 5.25 V and may be different to the voltage range at AV _{DD} and DV _{DD} but must never exceed either by more than 0.3 V.
20B	-159	-1820	V _{DRIVE}	Double	Logic Power Supply Input. The voltage supplied at this pin determines at what voltage the interface operates. Decouple this pin to DGND. The voltage range on this pin is 2.3 V to 5.25 V and may be different to the voltage range at AV _{DD} and DV _{DD} but must never exceed either by more than 0.3 V.
21A	+130	-1820	DGND	Double	Digital Ground. This pin is a ground reference point for the digital circuitry on the AD2S1210-KGD-CHIPS . Refer all digital input signals to this DGND voltage. Both DGND pins can be connected to the AGND plane of a system. Ideally, the DGND and AGND voltages are at the same potential, and they must not be more than 0.3 V apart, even on a transient basis.
21B	+201	-1820	DGND	Double	Digital Ground. This pin is a ground reference point for the digital circuitry on the AD2S1210-KGD-CHIPS . Refer all digital input signals to this DGND voltage. Both DGND pins can be connected to the AGND plane of a system. Ideally, the DGND and AGND voltages are at the same potential, and they must not be more than 0.3 V apart, even on a transient basis.
22	+519	-1820	DB8	Single	Data Bit 8. Three-state data output pin controlled by $\overline{\text{CS}}$ and $\overline{\text{RD}}$.
23	+663	-1820	DB7	Single	Data Bit 7. Three-state data input/output pin controlled by $\overline{\text{CS}}$, $\overline{\text{RD}}$, and $\overline{\text{WR/FSYNC}}$.
24	+1024	-1820	DB6	Single	Data Bit 6. Three-state data input/output pin controlled by $\overline{\text{CS}}$, $\overline{\text{RD}}$, and $\overline{\text{WR/FSYNC}}$.
25	+1167	-1820	DB5	Single	Data Bit 5. Three-state data input/output pin controlled by $\overline{\text{CS}}$, $\overline{\text{RD}}$, and $\overline{\text{WR/FSYNC}}$.
26	+1532	-1820	DB4	Single	Data Bit 4. Three-state data input/output pin controlled by $\overline{\text{CS}}$, $\overline{\text{RD}}$, and $\overline{\text{WR/FSYNC}}$.
27	+1870	-1441	DB3	Single	Data Bit 3. Three-state data input/output pin controlled by $\overline{\text{CS}}$, $\overline{\text{RD}}$, and $\overline{\text{WR/FSYNC}}$.

Pad No.	X-Axis (μm)	Y-Axis (μm)	Mnemonic	Pad Type	Description
28	+1870	-1080	DB2	Single	Data Bit 2. Three-state data input/output pin controlled by \overline{CS} , \overline{RD} , and $\overline{WR/FSYNC}$.
29	+1870	-937	DB1	Single	Data Bit 1. Three-state data input/output pin controlled by \overline{CS} , \overline{RD} , and $\overline{WR/FSYNC}$.
30	+1870	-576	DB0	Single	Data Bit 0. Three-state data input/output pin controlled by \overline{CS} , \overline{RD} , and $\overline{WR/FSYNC}$.
31	+1870	-433	A	Single	Incremental Encoder Emulation Output A. Logic output. This output is free running and valid if the resolver format input signals applied to the converter are valid.
32	+1870	-72	B	Single	Incremental Encoder Emulation Output B. Logic output. This output is free running and valid if the resolver format input signals applied to the converter are valid.
33	+1870	+72	NM	Single	North Marker Incremental Encoder Emulation Output. Logic output. This output is free running and valid if the resolver format input signals applied to the converter are valid.
34	+1870	+432	DIR	Single	Direction. Logic Output. This output is used in conjunction with the incremental encoder emulation outputs. The DIR output indicates the direction of the input rotation and is high for increasing angular rotation.
35	+1870	+576	\overline{RESET}	Single	Reset. Logic input. The AD2S1210-KGD-CHIPS requires an external reset signal to hold the RESET input low until V_{DD} is within the specified operating range of 4.75 V to 5.25 V.
36	+1870	+937	LOT	Single	Loss of Tracking. Logic output. LOT is indicated by a logic low on the LOT pin and is not latched.
37	+1870	+1080	DOS	Single	Degradation of Signal. Logic output. Degradation of signal (DOS) is detected when either resolver input (sine or cosine) exceeds the specified DOS sine/cosine threshold, or when an amplitude mismatch occurs between the sine and cosine input voltages. DOS is indicated by a logic low on the DOS pin.
38	+1870	+1441	A1	Single	Mode Select 1. Logic input. A1 in conjunction with A0 allows the selection of the mode of the AD2S1210-KGD-CHIPS.
39	+1580	+1820	A0	Single	Mode Select 0. Logic input. A0 in conjunction with A1 allows the selection of the mode of the AD2S1210-KGD-CHIPS.
40	+1031	+1820	EXC	Single	Excitation Frequency. Analog output. An on-board oscillator provides the sinusoidal excitation signal (EXC) and its complement signal (EXC) to the resolver. The frequency of this reference signal is programmable via the excitation frequency register.
41	+859	+1820	\overline{EXC}	Single	Excitation Frequency Complement. Analog output. An on-board oscillator provides the sinusoidal excitation signal (EXC) and its complement signal (EXC) to the resolver. The frequency of this reference signal is programmable via the excitation frequency register.
42A	+678	+1820	AGND	Double	Analog Ground. This pin is the ground reference point for the analog circuitry on the AD2S1210-KGD-CHIPS. Refer all analog input signals and any external reference signal to this AGND voltage. Connect the AGND pin to the AGND plane of a system. Ideally, the AGND and DGND voltages are at the same potential and must not be more than 0.3 V apart, even on a transient basis.
42B	+607	+1820	AGND	Double	Analog Ground. This pin is the ground reference point for the analog circuitry on the AD2S1210-KGD-CHIPS. Refer all analog input signals and any external reference signal to this AGND voltage. Connect the AGND pin to the AGND plane of a system. Ideally, the AGND and DGND voltages are at the same potential and must not be more than 0.3 V apart, even on a transient basis.
43	+440	+1820	SIN	Single	Positive Analog Input of Differential SIN/SINLO Pair. The input range is 2.3 V p-p to 4.0 V p-p.
44	+262	+1820	SINLO	Single	Negative Analog Input of Differential SIN/SINLO Pair. The input range is 2.3 V p-p to 4.0 V p-p.

Pad No.	X-Axis (μm)	Y-Axis (μm)	Mnemonic	Pad Type	Description
45A	+12	+1820	AV _{DD}	Double	Analog Supply Voltage, 4.75 V to 5.25 V. This pin is the supply voltage for all analog circuitry on the AD2S1210-KGD-CHIPS . Ideally, the AV _{DD} and DV _{DD} voltages ideally are at the same potential and must not be more than 0.3 V apart, even on a transient basis.
45B	-59	+1820	AV _{DD}	Double	Analog Supply Voltage, 4.75 V to 5.25 V. This pin is the supply voltage for all analog circuitry on the AD2S1210-KGD-CHIPS . Ideally, the AV _{DD} and DV _{DD} voltages ideally are at the same potential and must not be more than 0.3 V apart, even on a transient basis.
46	-411	+1820	COSLO	Single	Negative Analog Input of Differential COS/COSLO Pair. The input range is 2.3 V p-p to 4.0 V p-p.
47	-586	+1820	COS	Single	Positive Analog Input of Differential COS/COSLO Pair. The input range is 2.3 V p-p to 4.0 V p-p.
48	-876	+1820	REFBYP	Single	Reference Bypass. Connect reference decoupling capacitors at this pin. Typical recommended values are 10 μF and 0.01 μF.
49	-1112	+1820	REFOUT	Single	Voltage Reference Output.
50	-1590	+1820	RES0	Single	Resolution Select 0. Logic input. RES0 in conjunction with RES1 allows the programming of the resolution of the AD2S1210-KGD-CHIPS .

OUTLINE DIMENSIONS

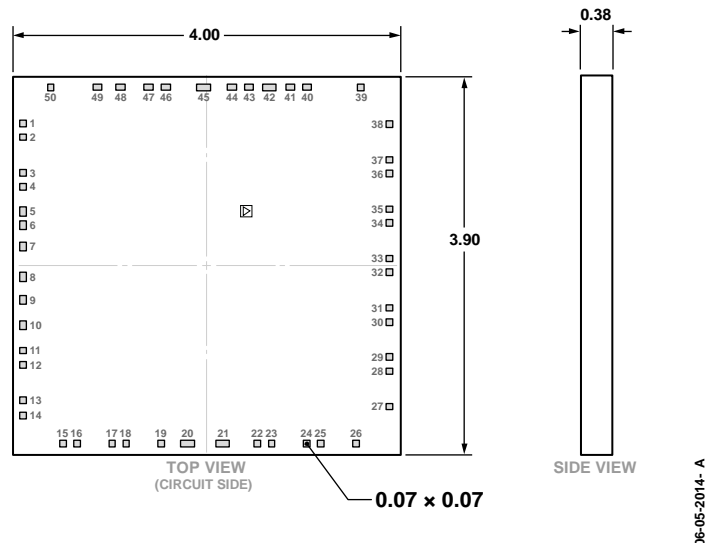


Figure 3. 50-Pad Bare Die [CHIP]
(C-50-1)
Dimensions shown in millimeters

DIE SPECIFICATIONS AND ASSEMBLY RECOMMENDATIONS

Table 5. Die Specifications

Parameter	Value	Unit
Chip Size	3920 (x) × 3820 (y)	μm
Scribe Line Width	80 (x) × 80 (y)	μm
Die Size	4000 (x) × 3900 (y)	μm
Thickness	380 ± 10	μm
Backside	Silicon	Not applicable
Passivation	Nitride	Not applicable
Bond Pads (Minimum)	70 × 70	μm
Bond Pad Composition	98.5% Al, 1% Si, 0.5% Cu	%
ESD	2	kV

Table 6. Assembly Recommendations

Assembly Component	Recommendation
Die Attach	No special recommendations
Bonding Method	Gold ball or aluminum wedge
Bonding Sequence	Pad 1 first

ORDERING GUIDE

Model	Temperature Range	Package Description	Package Option
AD2S1210-KGD-CHIPS	-55°C to +125°C	50-Pad Bare Die [CHIP], Waffle Pack	C-50-1